

Silicon NPN Power Transistors

2SD1425

DESCRIPTION

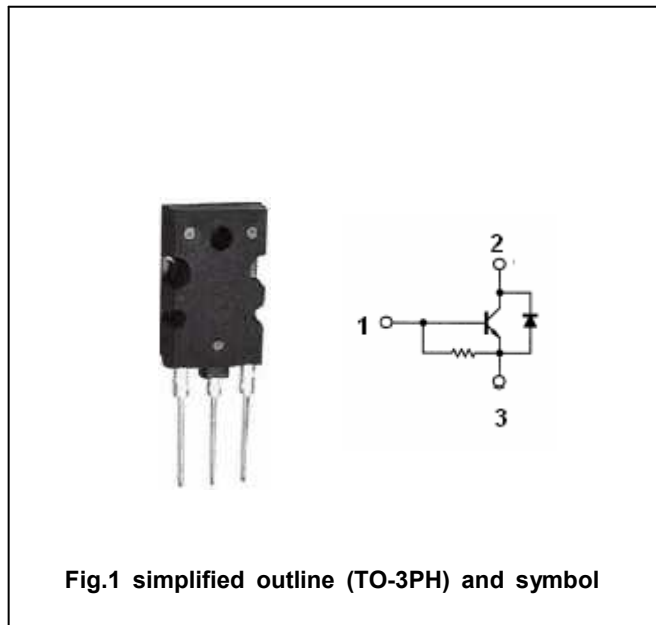
- With TO-3PH package
- Built-in damper diode
- High voltage ,high speed
- Low collector saturation voltage

APPLICATIONS

- Designed for use in color TV deflection circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		2.5	A
I _B	Base current		1.0	A
P _D	Total power dissipation	T _C =25℃	80	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction case	1.56	℃/W

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=200mA$; $I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2A$; $I_B=0.6A$			8.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2A$; $I_B=0.6A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=500V$; $I_E=0$			10	μA
h_{FE}	DC current gain	$I_C=0.5A$; $V_{CE}=5V$	8			
f_T	Transition frequency	$I_C=0.1A$; $V_{CE}=10V$; $f=1MHz$		3		MHz
C_{OB}	Output capacitance	$I_E=0$; $V_{CB}=10V$; $f=1.0MHz$		95		pF
V_F	Diode forward voltage	$I_F=2.5A$			2.0	V
t_f	Fall time	$I_C=2A$; $I_{B1}=0.6A$			1.0	μs

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PACKAGE OUTLINE

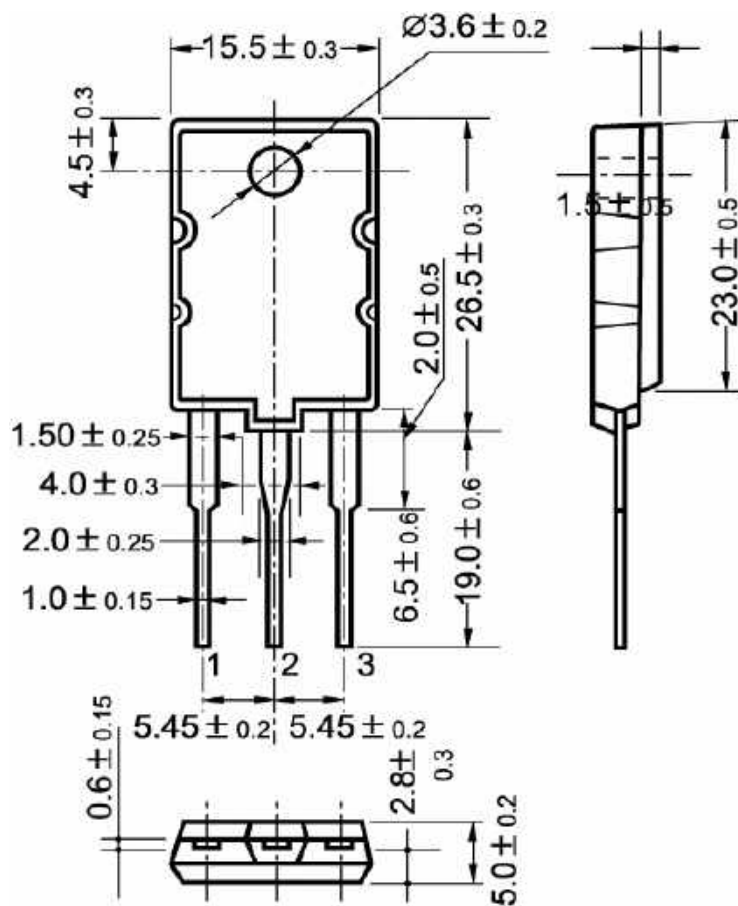


Fig.2 outline dimensions